



FEATURES

- High reliability LPE GaAlAs IRLED chips
- Graded-bandgap LED structure for high radiant power output
- 880nm peak emission
- Good ohmic contacts (gold alloys)
- Provides power output below 1mA

All dimensions are nominal values in inches unless otherwise specified.

PRODUCT DESCRIPTION

The OD-11X11-C is a smaller version of the OD-880-C. This chip is intended for use in very low current applications, such as solid state relays. Its smaller size results in a higher current density and much higher power output at currents less than 1mA.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P _o	I _F = 50mA	4	6		mW
	I _F = 20mA		2		
Peak Emission Wavelength, λ _p	I _F = 20mA		880		nm
Spectral Bandwidth at 50%, Δλ				80	
Forward Voltage, V _F	I _F = 20mA		1.35	1.6	Volts
Reverse Breakdown Voltage, V _R	I _R = 10μA	5	30		Volts
Rise Time			0.5		μsec
Fall Time			0.5		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C

Power Dissipation	100mW
Continuous Forward Current	60mA
Reverse Voltage	5V
Storage and Operating Temperature Range	-65°C to 150°C
Maximum Junction Temperature	150°C

The exact performance data depends on your package configuration and technique. Data listed in this specification is for the chip mounted on a TO-46 header using silver epoxy as the die attach material. All sales are final after 60 days from the shipment date. Opto Diode must be notified of any discrepancies within this period.



TYPICAL CHARACTERISTICS

